



2N3500

Silicon NPN Transistor

Data Sheet

Description

Semicoa Semiconductors offers:

- Screening and processing per MIL-PRF-19500 Appendix E
- JAN level (2N3500J)
- JANTX level (2N3500JX)
- JANTXV level (2N3500JV)
- QCI to the applicable level
- 100% die visual inspection per MIL-STD-750 method 2072 for JANTXV and JANS
- Radiation testing (total dose) upon request

Applications

- General purpose
- Low power
- NPN silicon transistor



Features

- Hermetically sealed TO-39 metal can
- Also available in chip configuration
- Chip geometry 5620
- Reference document: MIL-PRF-19500/366

Benefits

- Qualification Levels: JAN, JANTX, and JANTXV
- Radiation testing available

Absolute Maximum Ratings

T_C = 25°C unless otherwise specified

Parameter	Symbol	Rating	Unit
Collector-Emitter Voltage	V _{CEO}	150	Volts
Collector-Base Voltage	V _{CBO}	150	Volts
Emitter-Base Voltage	V _{EBO}	6	Volts
Collector Current, Continuous	I _C	300	mA
Power Dissipation, T _A = 25°C Derate linearly above 25°C	P _T	1 5.71	W mW/°C
Thermal Resistance	R _{θJA}	175	°C/W
Operating Junction Temperature	T _J	-65 to +200	°C
Storage Temperature	T _{STG}	-65 to +200	°C

Please contact Semicoa for special configurations
www.SEMICOA.com or (714) 979-1900

ELECTRICAL CHARACTERISTICS

 characteristics specified at $T_A = 25^\circ\text{C}$

Off Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Collector-Emitter Breakdown Voltage	$V_{(\text{BR})\text{CEO}}$	$I_C = 10 \text{ mA}$	150			Volts
Collector-Base Cutoff Current	$I_{\text{CBO}1}$ $I_{\text{CBO}2}$ $I_{\text{CBO}3}$	$V_{\text{CB}} = 150 \text{ Volts}$ $V_{\text{CB}} = 75 \text{ Volts}$ $V_{\text{CB}} = 75 \text{ Volts}, T_A = 150^\circ\text{C}$			10 50 50	μA nA μA
Collector-Emitter Cutoff Current	I_{CEO}	$V_{\text{CE}} = 120 \text{ Volts}$			1	μA
Emitter-Base Cutoff Current	$I_{\text{EBO}1}$ $I_{\text{EBO}2}$	$V_{\text{EB}} = 6 \text{ Volts}$ $V_{\text{EB}} = 4 \text{ Volts}$			10 25	μA nA

On Characteristics

 Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
DC Current Gain	$h_{\text{FE}1}$ $h_{\text{FE}2}$ $h_{\text{FE}3}$ $h_{\text{FE}4}$ $h_{\text{FE}5}$ $h_{\text{FE}7}$	$I_C = 0.1 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$ $I_C = 1.0 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$ $I_C = 10 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$ $I_C = 150 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$ $I_C = 300 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$ $I_C = 150 \text{ mA}, V_{\text{CE}} = 10 \text{ Volts}$ $T_A = -55^\circ\text{C}$	20 25 35 40 15 22		120	
Base-Emitter Saturation Voltage	$V_{\text{BEsat}1}$ $V_{\text{BEsat}2}$	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$ $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$			0.8 1.2	Volts
Collector-Emitter Saturation Voltage	$V_{\text{CESat}1}$ $V_{\text{CESat}2}$	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$ $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$			0.2 0.4	Volts

Dynamic Characteristics

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Magnitude – Common Emitter, Short Circuit Forward Current Transfer Ratio	$ h_{\text{FE}} $	$V_{\text{CE}} = 20 \text{ Volts}, I_C = 20 \text{ mA}, f = 100 \text{ MHz}$	1.5		8	
Small Signal Short Circuit Forward Current Transfer Ratio	h_{FE}	$V_{\text{CE}} = 10 \text{ Volts}, I_C = 10 \text{ mA}, f = 1 \text{ kHz}$	35		300	
Open Circuit Output Capacitance	C_{OBO}	$V_{\text{CB}} = 10 \text{ Volts}, I_E = 0 \text{ mA}, 100 \text{ kHz} < f < 1 \text{ MHz}$			8	pF
Open Circuit Input Capacitance	C_{IBO}	$V_{\text{EB}} = 0.5 \text{ Volts}, I_C = 0 \text{ mA}, 100 \text{ kHz} < f < 1 \text{ MHz}$			80	pF
Noise Figure	NF_1 NF_2	$V_{\text{CE}} = 10 \text{ Volts}, I_C = 0.5 \text{ mA}, f = 1 \text{ kHz}, R_g = 1 \text{ k}\Omega$ $V_{\text{CE}} = 10 \text{ Volts}, I_C = 0.5 \text{ mA}, f = 10 \text{ kHz}, R_g = 1 \text{ k}\Omega$			16 6	dB

Switching Characteristics

Saturated Turn-On Time	t_{ON}	$V_{\text{EB}} = 5 \text{ Volts}, I_C = 150 \text{ mA}, I_{\text{B}1} = 15 \text{ mA}$			115	ns
Saturated Turn-Off Time	t_{OFF}	$I_C = 150 \text{ mA}, I_{\text{B}1} = I_{\text{B}2} = 15 \text{ mA}$			1,150	ns